

**IN THE CLAIMS:**

Please amend claim 4 and add new claims 14-19 as follows:

A1  
Sub C7

4. (Amended) A semiconductor device comprising:  
a substrate;  
a source/drain diffused layer formed in the substrate for a transistor; and  
a dummy diffused layer formed in the substrate;  
wherein the source/drain diffused layer has its surface silicided, and  
wherein the dummy diffused layer has its surface covered with a dummy gate electrode at  
least partially.

A2  
Sub B2

14. (New) The device of claim 1, wherein the dummy diffused layer is located  
between a circuit block and another circuit block.

B

15. (New) The device of claim 1, wherein the dummy diffused layer is not  
electrically coupled to another component via an interconnect.

Sub C7

16. (New) The device of claim 4, wherein the dummy diffused layer is located  
between a circuit block and another circuit block.

17. (New) The device of claim 4, wherein the dummy diffused layer is not  
electrically coupled to another component via an interconnect.

18. (New) A method of making a semiconductor device comprising:

B